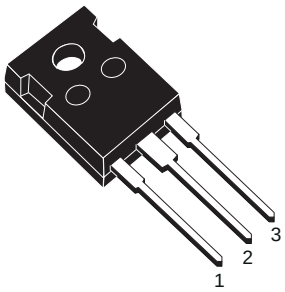
STW20NM50

N-CHANNEL 500V - 0.20Ω - 20A TO-247
MDmesh™Power MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STW20NM50	500V	< 0.25Ω	20 A

- TYPICAL $R_{DS}(on)$ = 0.20Ω
- HIGH dv/dt AND AVALANCHE CAPABILITIES
- 100% AVALANCHE TESTED
- LOW INPUT CAPACITANCE AND GATE CHARGE
- LOW GATE INPUT RESISTANCE
- TIGHT PROCESS CONTROL AND HIGH MANUFACTURING YIELDS



TO-247

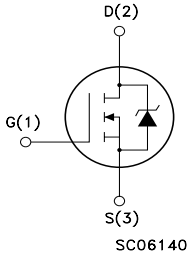
DESCRIPTION

The MDmesh™ is a new revolutionary MOSFET technology that associates the Multiple Drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competition's products.

APPLICATIONS

The MDmesh™ family is very suitable for increasing power density of high voltage converters allowing system miniaturization and higher efficiencies.

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	500	V
V_{DGR}	Drain-gate Voltage (R_{GS} = 20 kΩ)	500	V
V_{GS}	Gate- source Voltage	±30	V
I_D	Drain Current (continuous) at T_C = 25°C	20	A
I_D	Drain Current (continuous) at T_C = 100°C	12.6	A
I_{DM} (•)	Drain Current (pulsed)	80	A
P_{TOT}	Total Dissipation at T_C = 25°C	214	W
	Derating Factor	1.44	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	15	V/ns
T_{stg}	Storage Temperature	–65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•)Pulse width limited by safe operating area

(1) I_{SD} ≤20A, di/dt ≤400A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_j ≤ $T_{JMAX.}$

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	0.585	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	30	°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	10	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, I_D = 5 A, V_{DD} = 35 V)	650	mJ

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA, V_{GS} = 0	500			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating			1	µA
		V_{DS} = Max Rating, T_C = 125 °C			100	µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ±30V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250µA	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10V, I_D = 10A		0.20	0.25	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward Transconductance	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max}$, I_D = 10A		10		S
C_{iss}	Input Capacitance	V_{DS} = 25V, f = 1 MHz, V_{GS} = 0		1480		pF
C_{oss}	Output Capacitance			285		pF
C_{rss}	Reverse Transfer Capacitance			34		pF
$C_{oss\ eq.}$ (2)	Equivalent Output Capacitance	V_{GS} = 0V, V_{DS} = 0V to 400V		130		pF
R_G	Gate Input Resistance	f=1 MHz Gate DC Bias = 0 Test Signal Level = 20mV Open Drain		1.6		Ω

1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

ELECTRICAL CHARACTERISTICS (CONTINUED)
SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	V_{DD} = 250V, I_D = 10 A		24		ns
t_r	Rise Time	R_G = 4.7Ω V_{GS} = 10 V (see test circuit, Figure 3)		16		ns
Q_g	Total Gate Charge	V_{DD} = 400 V, I_D = 20 A, V_{GS} = 10 V		40	56	nC
Q_{gs}	Gate-Source Charge			13		nC
Q_{gd}	Gate-Drain Charge			19		nC

SWITCHING OFF

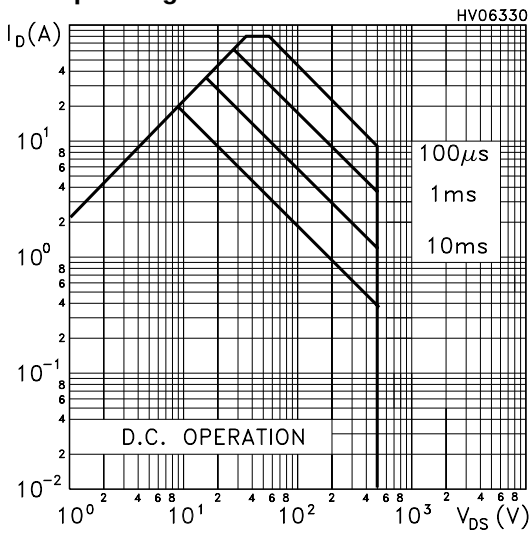
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	V_{DD} = 400 V, I_D = 20 A, R_G = 4.7Ω, V_{GS} = 10 V (see test circuit, Figure 5)		9		ns
t_f	Fall Time			8.5		ns
t_c	Cross-over Time			23		ns

SOURCE DRAIN DIODE

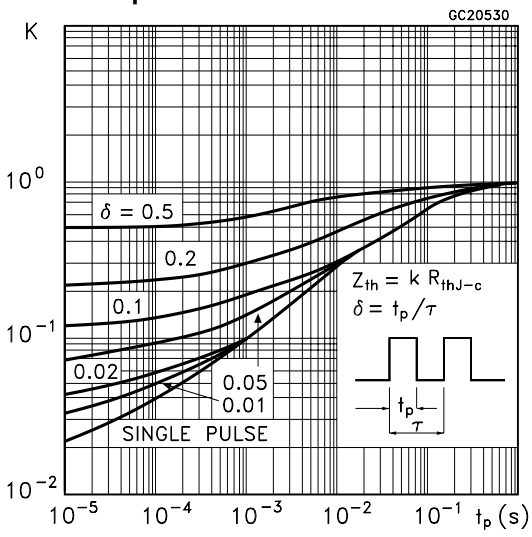
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				20	A
I_{SDM} (2)	Source-drain Current (pulsed)				80	A
V_{SD} (1)	Forward On Voltage	I_{SD} = 20 A, V_{GS} = 0			1.5	V
t_{rr}	Reverse Recovery Time	I_{SD} = 20 A, di/dt = 100 A/µs, V_{DD} = 100 V, T_j = 25°C (see test circuit, Figure 5)		350		ns
Q_{rr}	Reverse Recovery Charge			4.6		µC
I_{rrm}	Reverse Recovery Current			26		A
t_{rr}	Reverse Recovery Time	I_{SD} = 20 A, di/dt = 100 A/µs, V_{DD} = 100 V, T_j = 150°C (see test circuit, Figure 5)		435		ns
Q_{rr}	Reverse Recovery Charge			5.9		µC
I_{rrm}	Reverse Recovery Current			27		A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

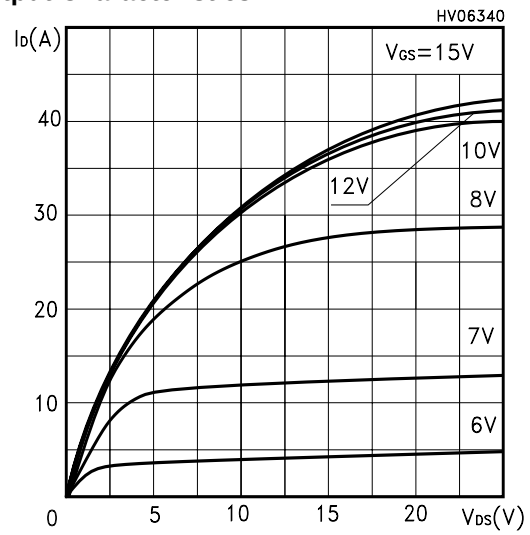
Safe Operating Area



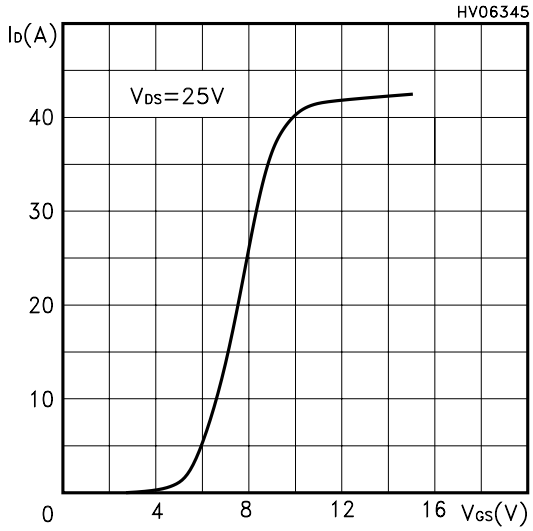
Thermal Impedance



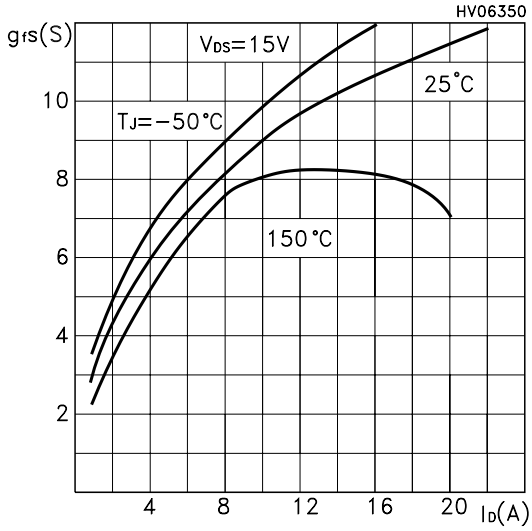
Output Characteristics



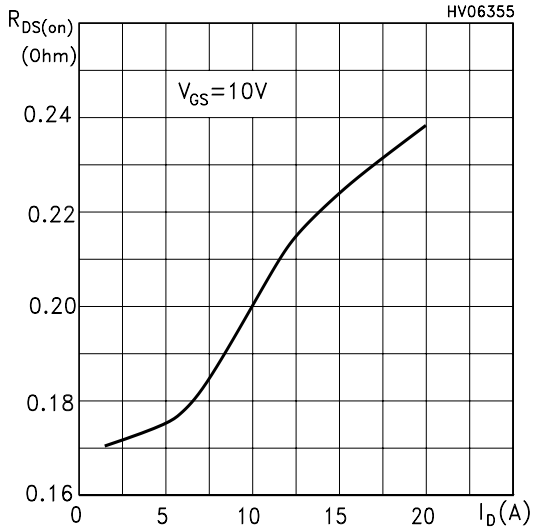
Transfer Characteristics



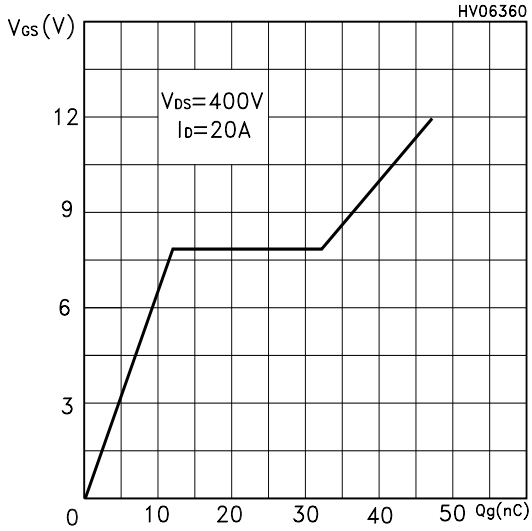
Transconductance



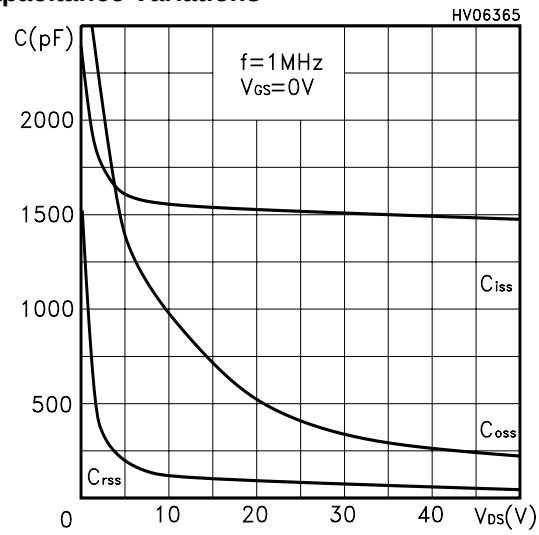
Static Drain-source On Resistance



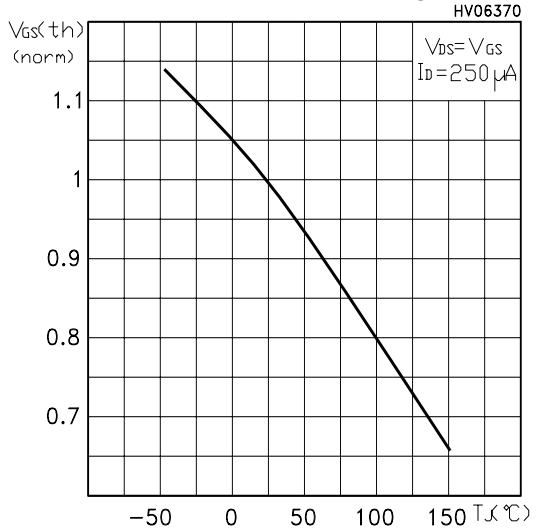
Gate Charge vs Gate-source Voltage



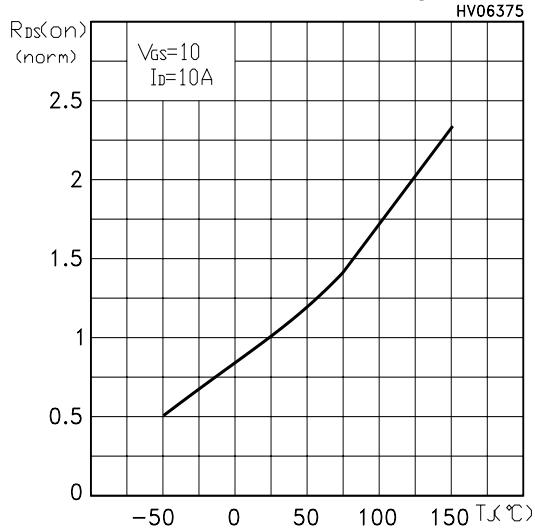
Capacitance Variations



Normalized Gate Thereshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

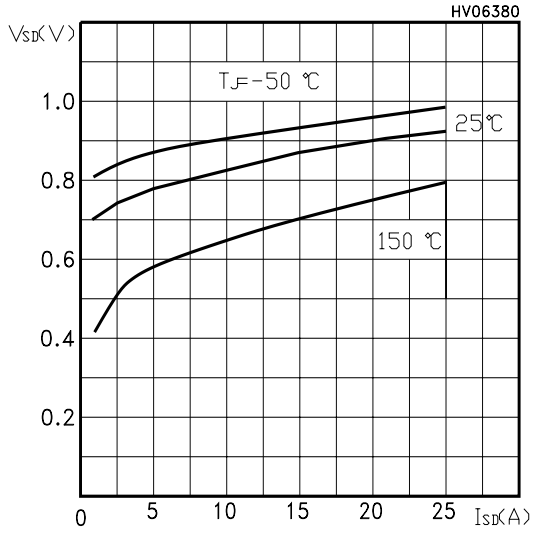


Fig. 1: Unclamped Inductive Load Test Circuit

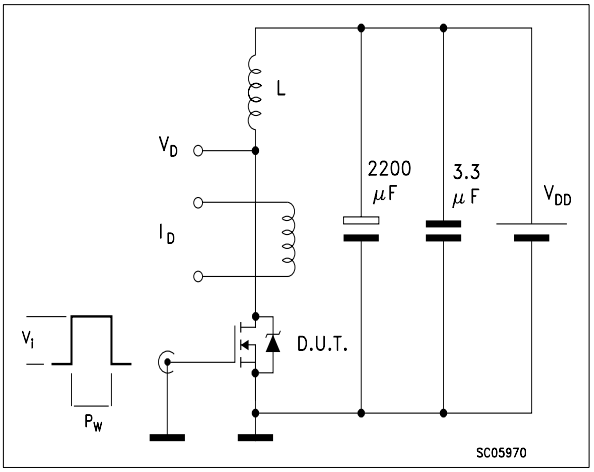


Fig. 2: Unclamped Inductive Waveform

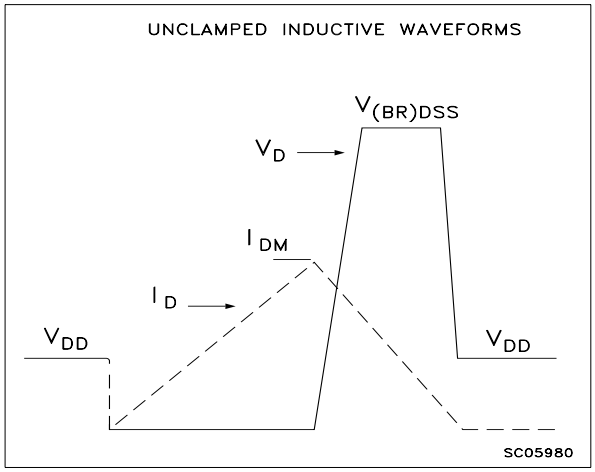


Fig. 3: Switching Times Test Circuit For Resistive Load

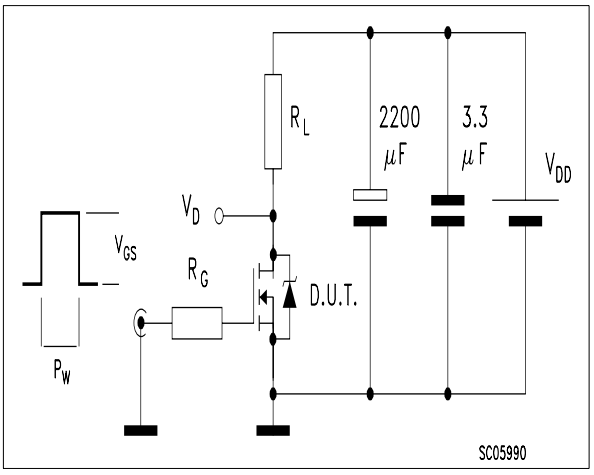


Fig. 4: Gate Charge test Circuit

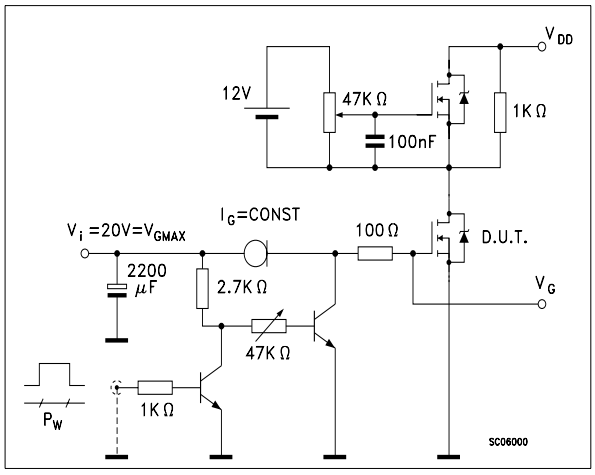
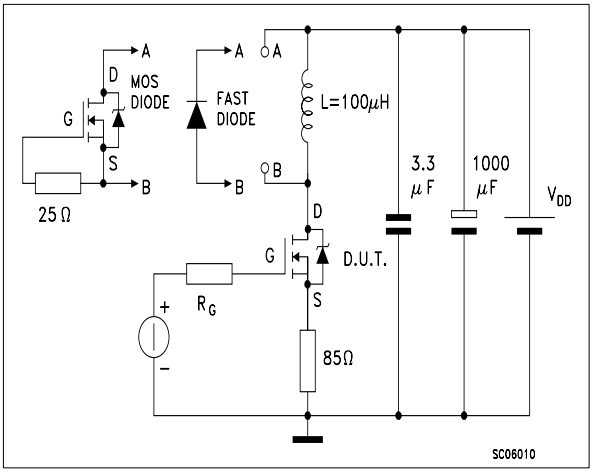
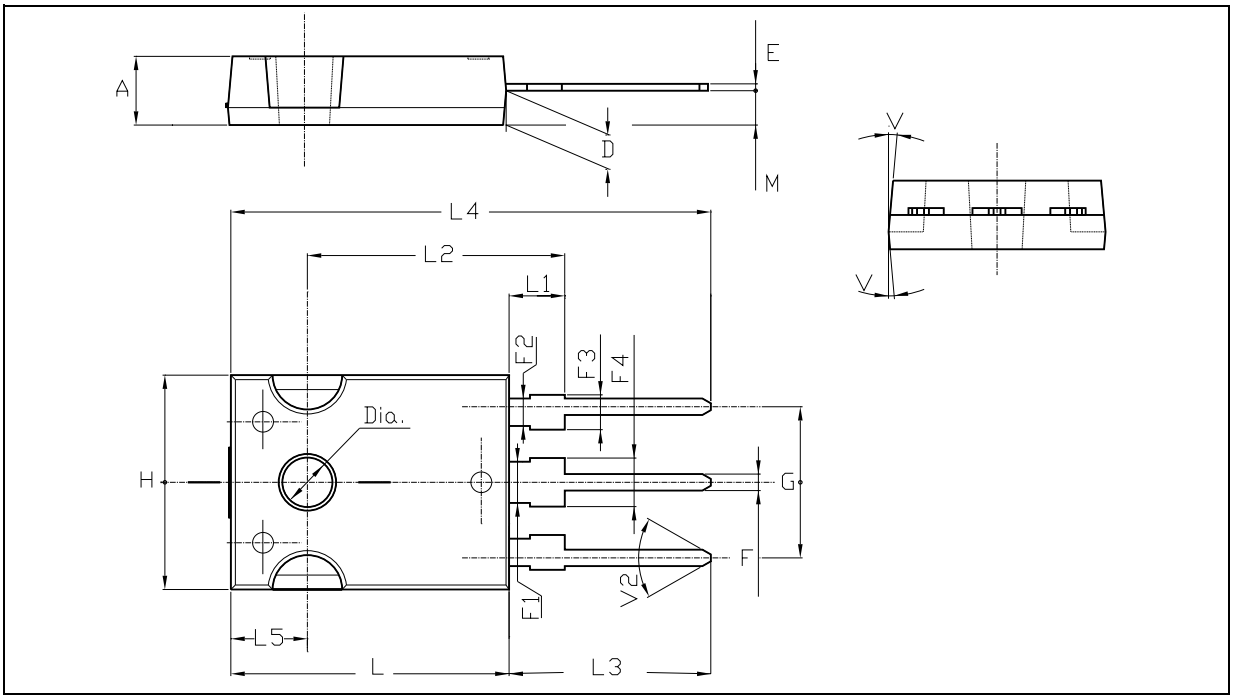


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
D	2.20		2.60	0.08		0.10
E	0.40		0.80	0.015		0.03
F	1		1.40	0.04		0.05
F1		3			0.11	
F2		2			0.07	
F3	2		2.40	0.07		0.09
F4	3		3.40	0.11		0.13
G		10.90			0.43	
H	15.45		15.75	0.60		0.62
L	19.85		20.15	0.78		0.79
L1	3.70		4.30	0.14		0.17
L2		18.50			0.72	
L3	14.20		14.80	0.56		0.58
L4		34.60			1.36	
L5		5.50			0.21	
M	2		3	0.07		0.11
V		5º			5º	
V2		60º			60º	
Dia	3.55		3.65	0.14		0.143



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